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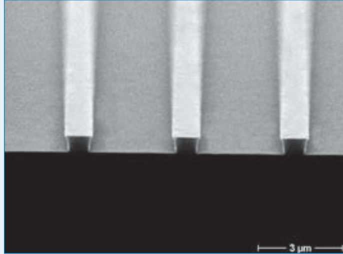
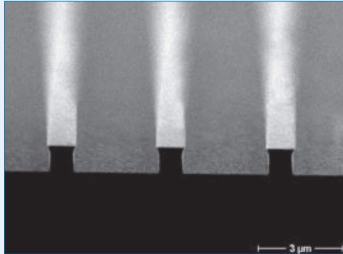
micro resist technology

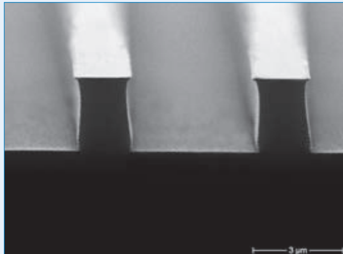
ma-P 1200 — Positive Tone Photoresist Series

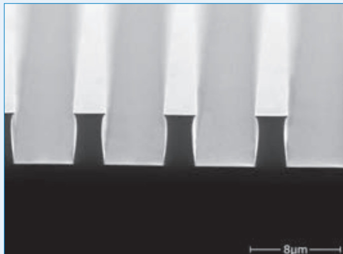
Resists for UV Lithography

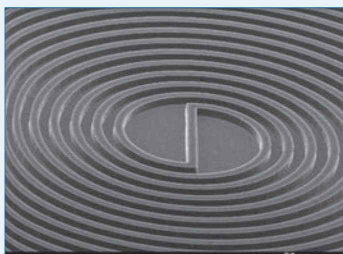
Resist patterning with mask aligner, broadband exposure

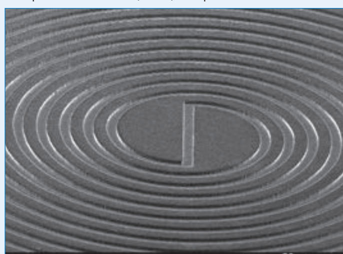

0.5 µm ma-P 1205, 1 µm lines, 3 µm spaces


1 µm ma-P 1210, 1 µm lines, 3 µm spaces


2.5 µm ma-P 1225, 2 µm lines, 4 µm spaces


4 µm ma-P 1240, 3 µm lines, 5 µm spaces


7.5 µm ma-P 1275, coil, 10 µm turns


5 µm electroplated Ni coil, 10 µm turns

ls.15.06.18

Unique features

- High pattern stability in wet etch processes and acid and alkaline plating baths
- Highly stable in dry etch processes e.g. CHF_3, CF_4, SF_6
- Aqueous alkaline development
- Easy to remove
- Resists available in a variety of viscosities

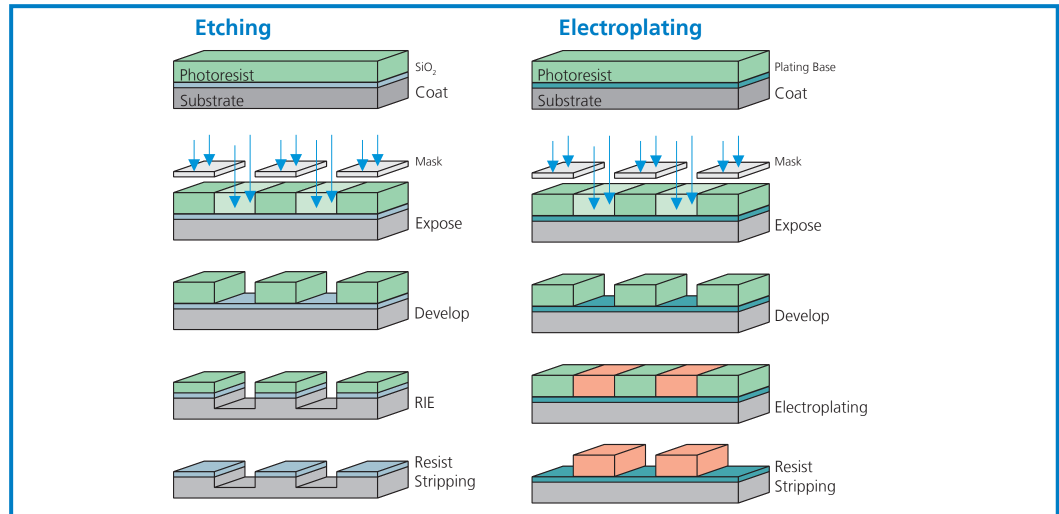
Applications

Mask for etching e.g.
- Si, SiO_2
- Metals
- Semiconductors

Mask for ion implantation

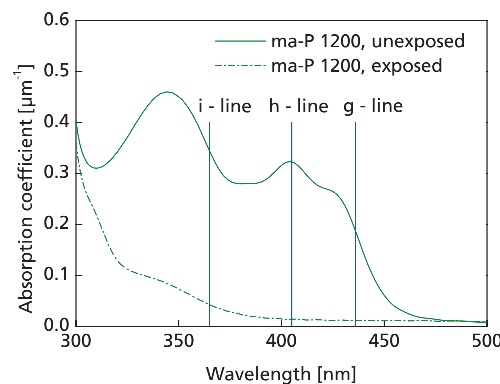
Mould for electroplating

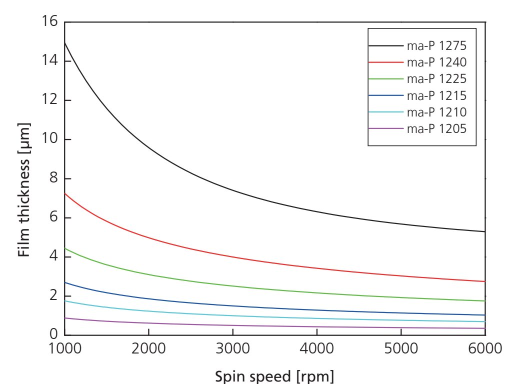
Process flow



Technical data

Resist		ma-P 1205	ma-P 1210	ma-P 1215	ma-P 1225	ma-P 1240	ma-P 1275
Film thickness	µm	0.5	1.0	1.5	2.5	4.0	7.5
Spin coating	rpm s	3000 30					
Spectral sensitivity		broadband, g-, h-, i-line					
Dose @ 365 nm (broadband exposure)	mJ cm^{-2}	35	35	45	55	110	150





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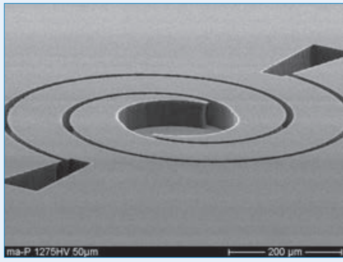
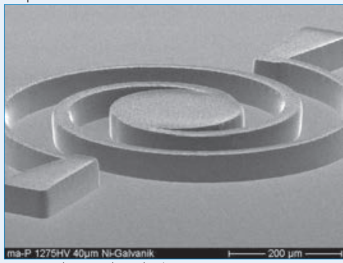
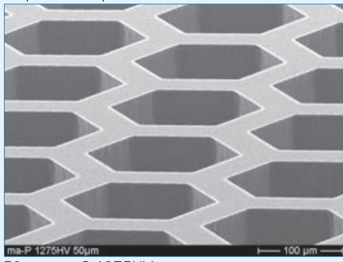
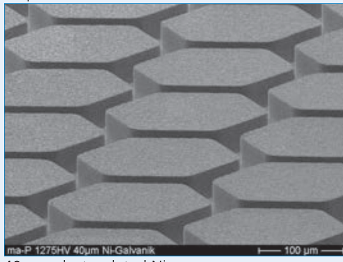
ma-P 1275 and ma-P 1275HV – Positive Tone Photoresists

Versatile high viscosity positive tone photoresists for microsystems technology

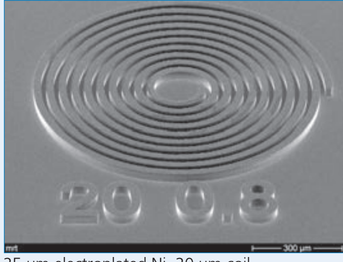

50 µm ma-P 1275HV


40 µm electroplated Ni


50 µm ma-P 1275HV


40 µm electroplated Ni

30 µm ma-P 1275HV, 20 µm coil


25 µm electroplated Ni, 20 µm coil

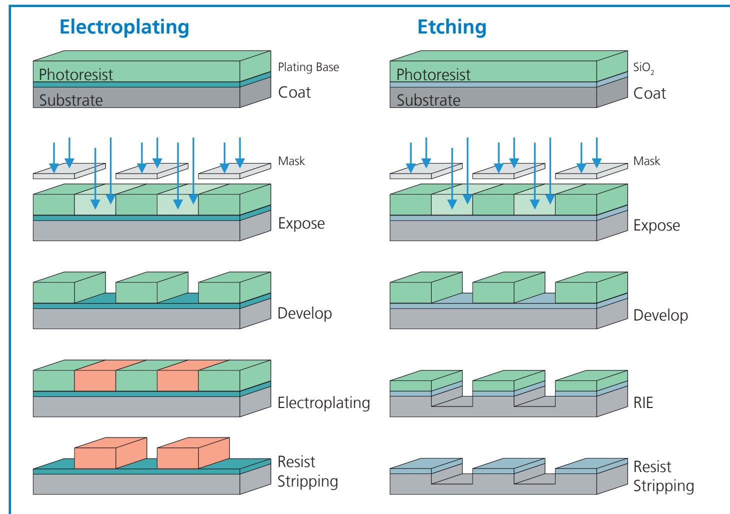
All resist patterns obtained by mask aligner broadband exposure

ls.15.06.18

Characteristics

- Specifically designed for electroplating of structures in microsystems technology
- High stability in acid and alkaline plating baths
- High dry and wet etch resistance
- Good thermal stability of the resist patterns attainable
- Aqueous alkaline development
- Easy to remove
- Side wall angle up to 87° with mask aligner broadband exposure
- Suitable for pattern reflow

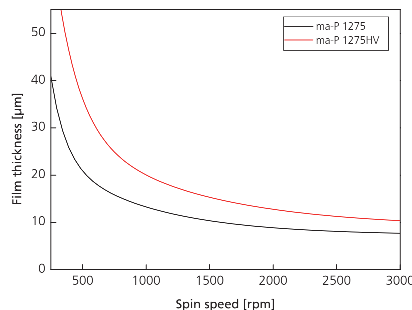
Process flow



Film thicknesses

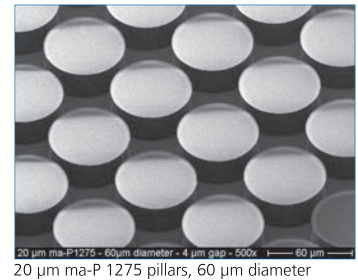
Film thickness	µm	7.5	11	20	30	40	50
ma-P 1275	rpm s	3000 30		500 60	350 60	250 60	–
ma-P 1275HV	rpm s	–	3000 30	1000 60	600 60	450 60	400 60

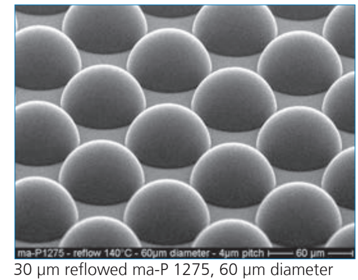
Spin curves

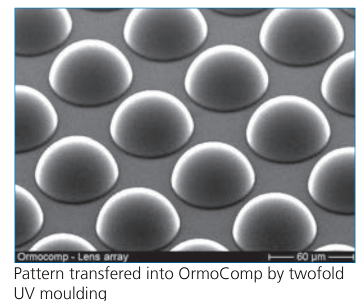


Applications

- Mould for electroplating
- Etch mask for metal and semiconductor substrates – e.g. microlenses from reflowed patterns
- Mask for ion implantation
- Mould for UV moulding after reflow


20 µm ma-P 1275 pillars, 60 µm diameter


30 µm reflowed ma-P 1275, 60 µm diameter


Pattern transfered into OrmoComp by twofold UV moulding

UV/vis spectra